ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	SUP90N06-6M0P-E3
Manufacturer:	Vishay Siliconix
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

https://antrexco.com/product/details/vishay-siliconix/sup90n06-6m0p-e3.html

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CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
60	0.006 at V_{GS} = 10 V	90[d]	78.5

FEATURES

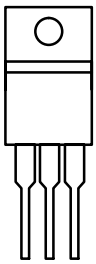
- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

APPLICATIONS

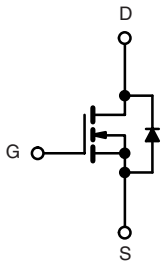
- Power Supply
  - Secondary Synchronous Rectification
- Industrial

TO-220AB



Top View

Ordering Information: SUP90N06-6m0P-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	90[d]	A
	T_C = 70 °C		90[d]	
Pulsed Drain Current		I_{DM}	240	
Avalanche Current		I_{AS}	50	
Single Avalanche Energy[a]	L = 0.1 mH	E_{AS}	125	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	272[b]	W
	T_A = 25 °C[c]		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.55	

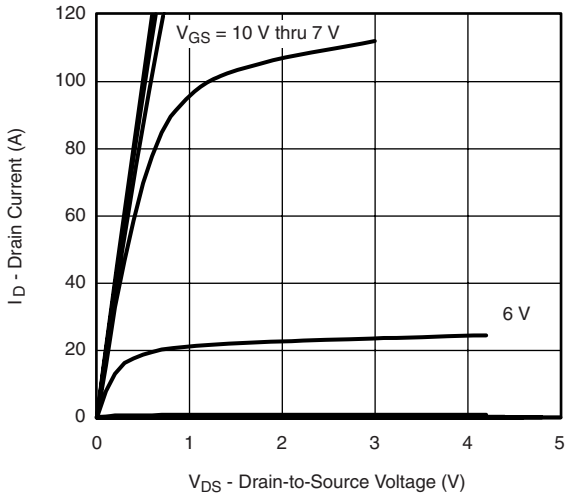
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When Mounted on 1" square PCB (FR-4 material).
d. Package limited.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{DS} = 0 V, I_D = 250 µA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.5		4.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 150 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 10 V, V_{GS} = 10 V	70			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.005	0.006	Ω
		V_{GS} = 10 V, I_D = 20 A, T_J = 125 °C		0.008	0.010	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 20 A		58		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 30 V, f = 1 MHz		4700		pF
Output Capacitance	C_{oss}			620		
Reverse Transfer Capacitance	C_{rss}			250		
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 50 A		78.5	120	nC
Gate-Source Charge[c]	Q_{gs}			28		
Gate-Drain Charge[c]	Q_{gd}			20.6		
Gate Resistance	R_g	f = 1 MHz		1.2	2.4	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.6 Ω I_D ≅ 50 A, V_{GEN} = 10 V, R_g = 1 Ω		16	30	ns
Rise Time[c]	t_r			10	20	
Turn-Off Delay Time[c]	$t_{d(off)}$			25	40	
Fall Time[c]	t_f			8	15	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				85	A
Pulsed Current	I_{SM}				240	
Forward Voltage[a]	V_{SD}	I_F = 20 A, V_{GS} = 0 V		0.83	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 75 A, dI/dt = 100 A/µs		62	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			3.8	5.7	A
Reverse Recovery Charge	Q_{rr}			118	180	nC

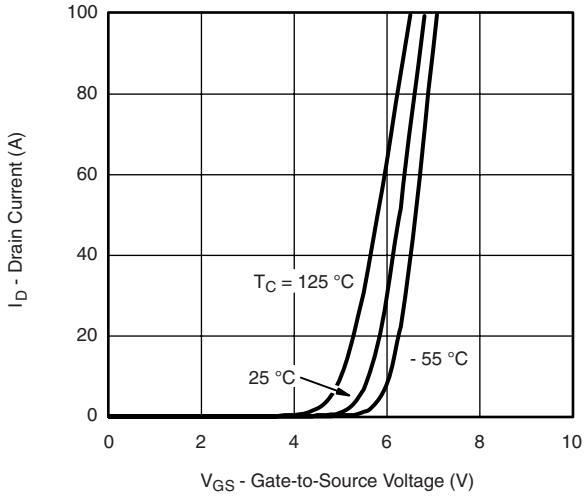
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

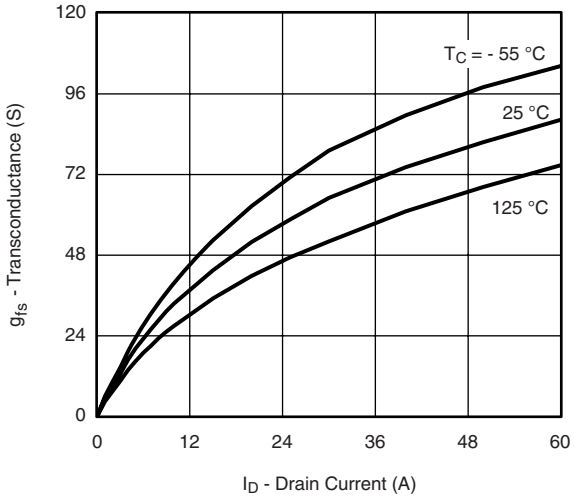
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



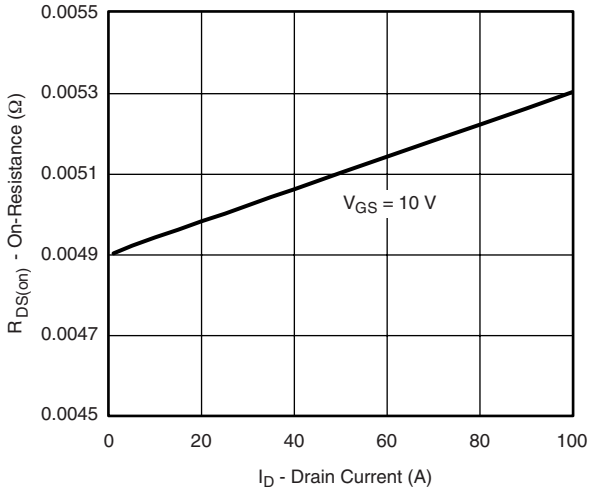
Output Characteristics



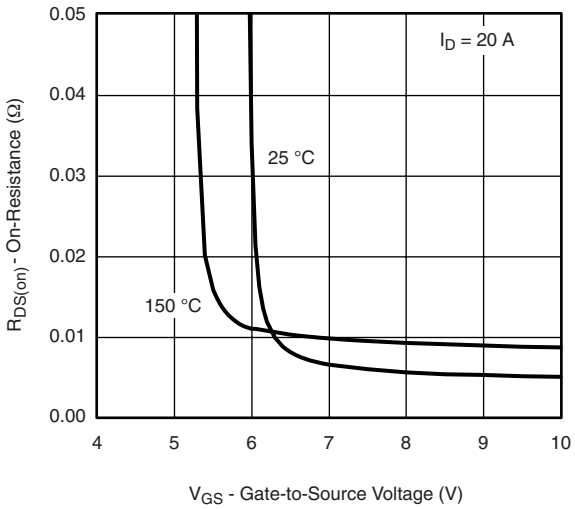
Transfer Characteristics



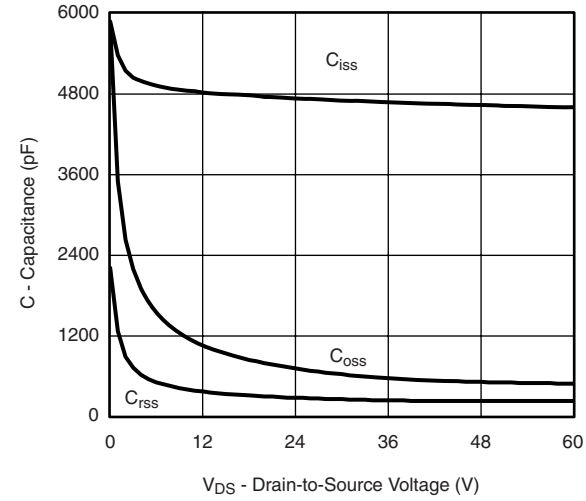
Transconductance



On-Resistance vs. Drain Current

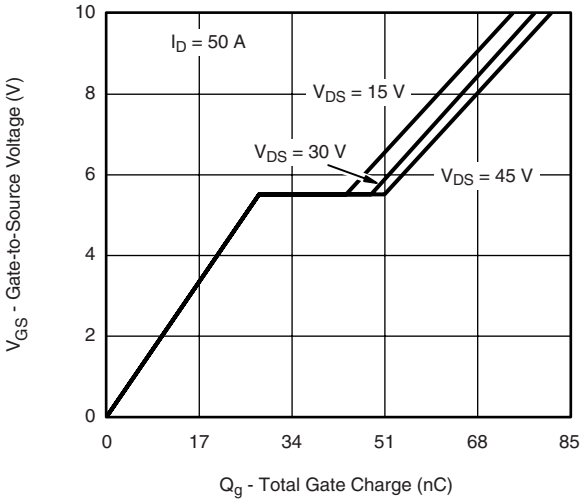


On-Resistance vs. Gate-to-Source Voltage

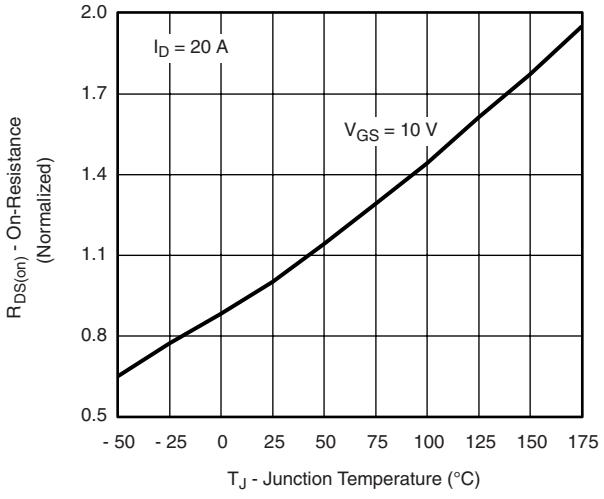


Capacitance

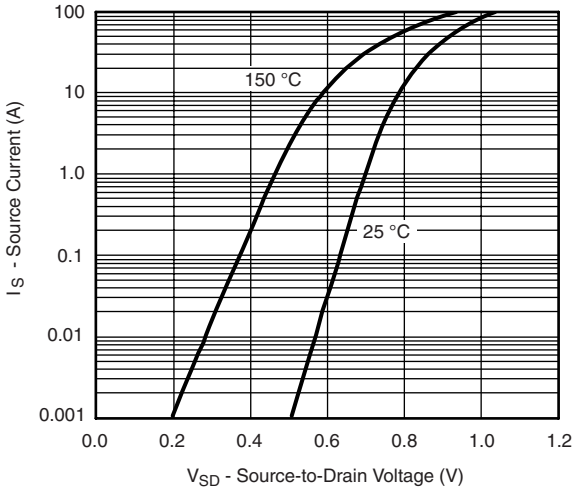
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



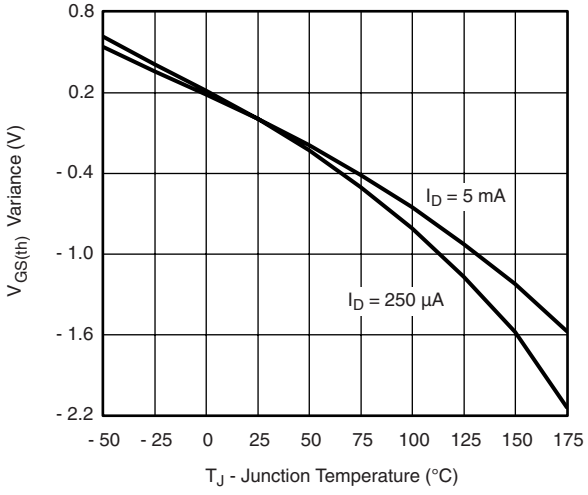
On-Resistance vs. Junction Temperature



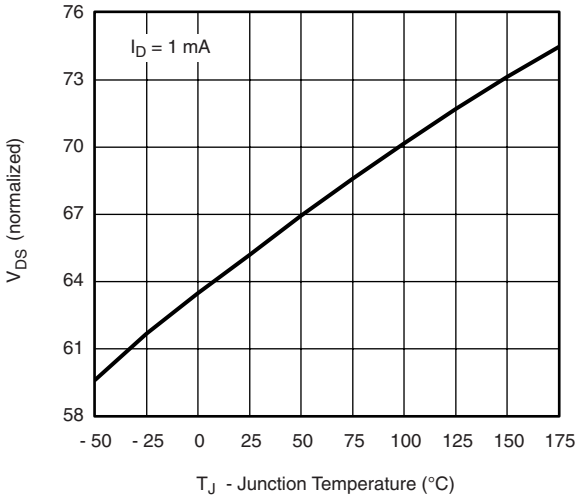
Threshold Voltage



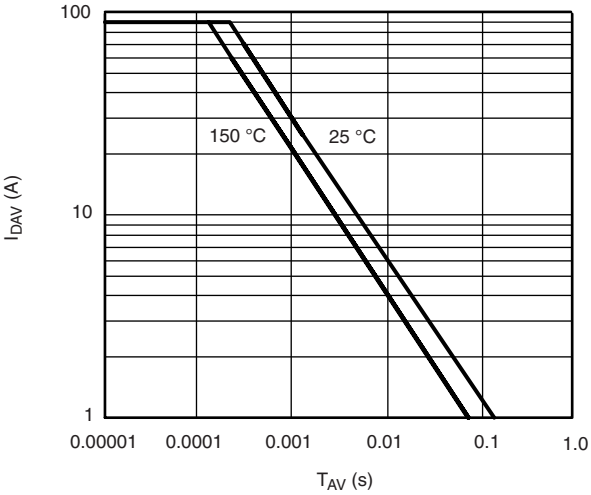
Gate Charge



On-Resistance vs. Junction Temperature

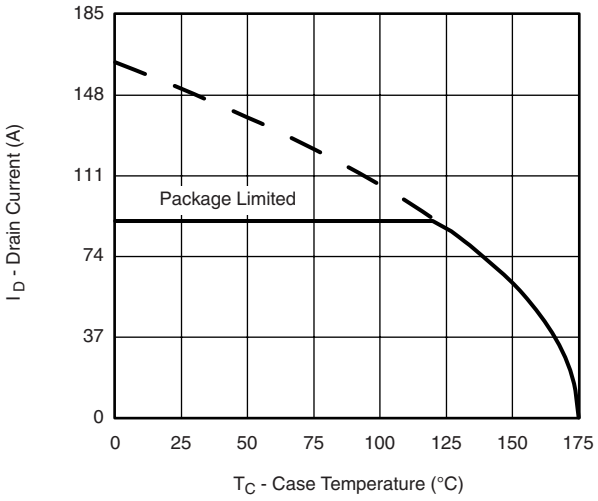


Source-Drain Diode Forward Voltage

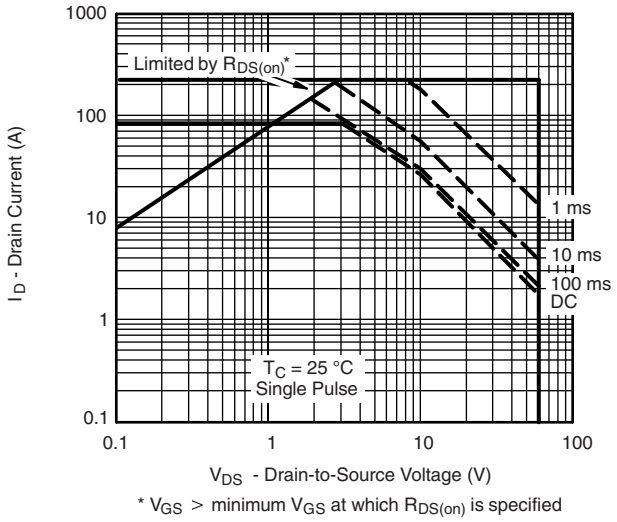


Maximum Drain Current vs. Case Temperature

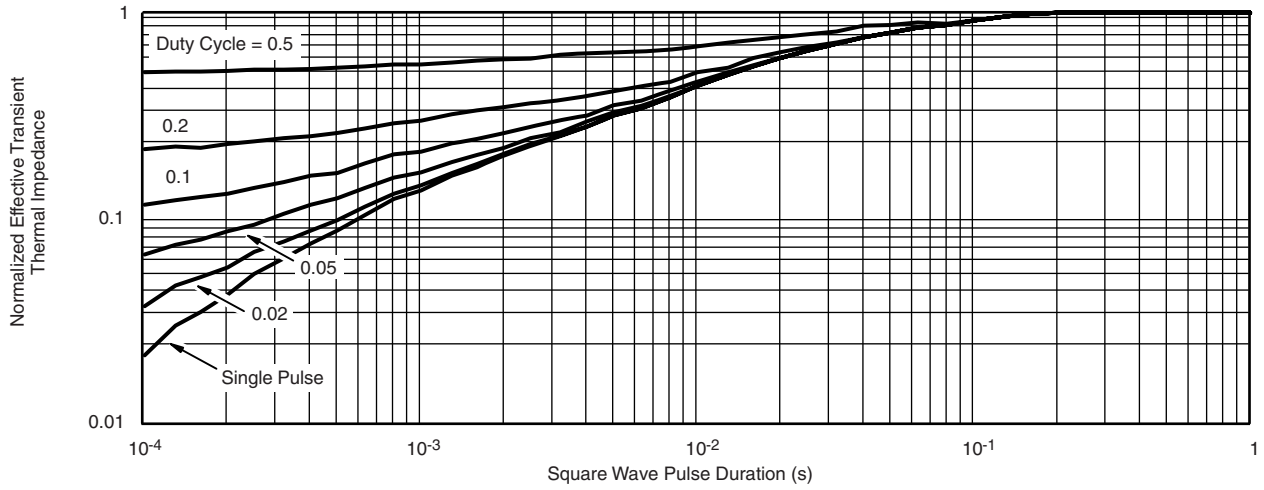
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Single Pulse Avalanche Current Capability vs. Time



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69536.

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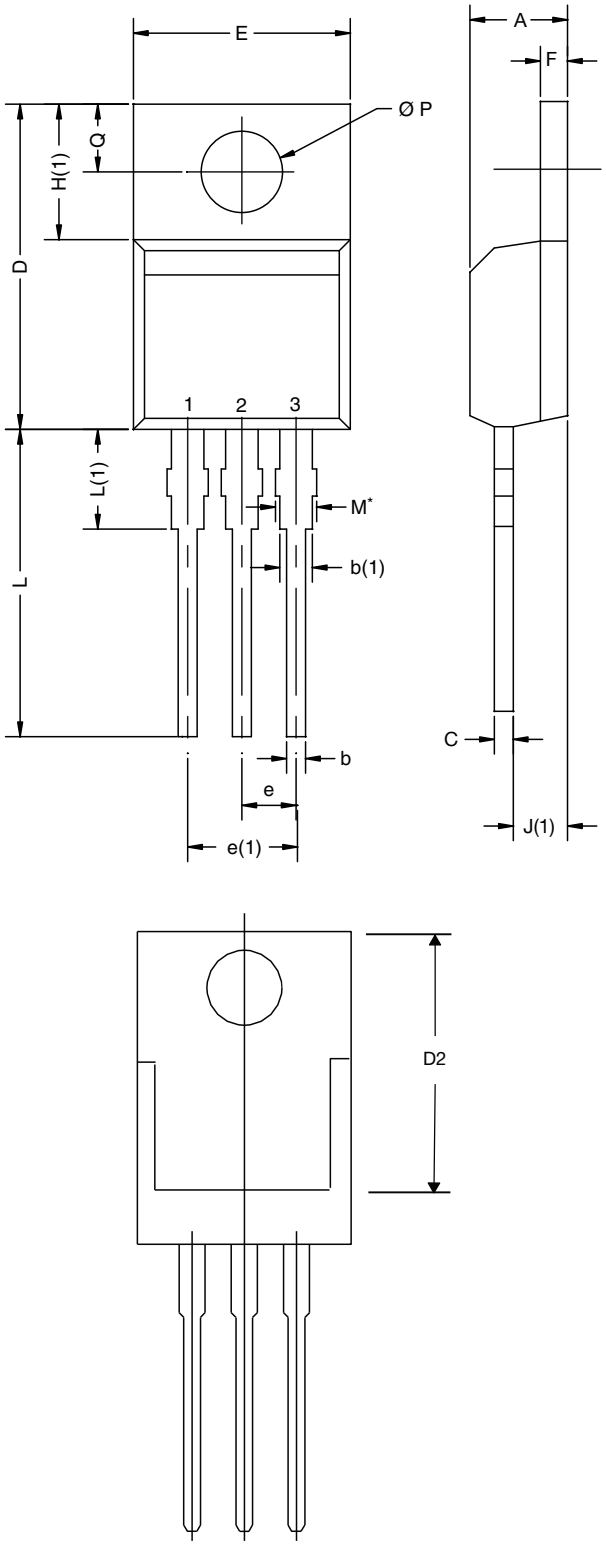

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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